Structured Electronic Design

Balancing: push-pull stage

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Complementary-parallel biased CS stages



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Common-mode currents are defined by the bias voltages and the device characteristics



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(VgsN) (3) (4) + E2 (4) V2 (4) V2 (10) I12 (10) I2 (10)

















Class A operation:

Sink and source devices conduct during push and pull phase

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Class B operation:

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Between A and B: overlap

- Sink device conducts during pull phase Source device conducts during push phase

Class B operation:

Class AB operation:

Class C operation:

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Dead zone

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Small-signal diagram push-pull stage

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Push-pull stage SLiCAP model

SLiCAP subcircuit for this symbol: CMOS18PN